XBS053V15R-G



Schottky Barrier Diode, 500mA, 30V Type

■FEATURES

Forward Voltage : V_F=0.40V (TYP.)

Forward Current : I_{F(AV)}=500mA

Repetitive Peak Reverse Voltage: V_{RM}=30V

Environmentally Friendly : EU RoHS Compliant, Pb Free

■APPLICATIONS

- Rectification
- Protection against reverse connection of battery

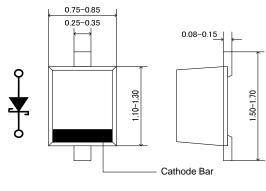
■ ABSOLUTE MAXIMUM RATINGS

Ta=25°C

PARAMETER	SYMBOL	RATINGS	UNIT	
Repetitive Peak Reverse Voltage	VRM	30	V	
Reverse Voltage (DC)	Vr	20	V	
Forward Current (Average)	I F(AV)	500	mA	
Non Continuous	IFSM	5	۸	
Forward Surge Current *1	IF5M	5	A	
Junction Temperature	Tj	125	°C	
Storage Temperature Range	Tstg	-55 ~ +150	°C	

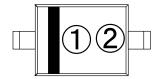
^{*1:} Non continuous high amplitude 60Hz half-sine wave.

■ PACKAGING INFORMATION





■MARKING RULE



- ①: 2 (Product Number)
- 2: Assembly Lot Number

■PRODUCT NAME

PRODUCT NAME	DEVICE ORIENTATION
XBS053V15R-G	SOD-523(Halogen & Antimony free)
XBS053V15R	SOD-523

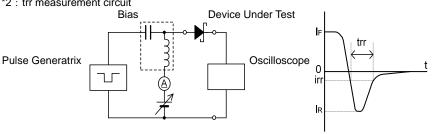
^{*} The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully RoHS compliant.

■ELECTRICAL CHARACTERISTICS

Ta=25°C

PARAMETER SYMBO	CVMDOL	TEST CONDITIONS	LIMITS			UNIT
	STIVIDOL		MIN.	TYP.	MAX.	UNIT
Forward Voltage ——	VF1	I _F =100mA	-	0.28	-	V
	VF2	I _F =500mA	-	0.40	0.47	V
Reverse Current	lr	V _R =20V	-	=	100	μΑ
Inter-Terminal Capacity	Ct	V _R =10V , f=1MHz	-	12	-	pF
Reverse Recovery Time *2	trr	I _F =I _R =10mA , irr=1mA	-	8	-	ns

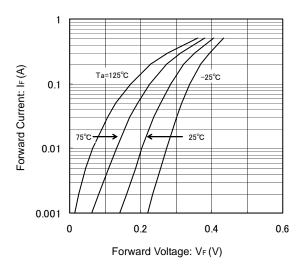
*2 : trr measurement circuit



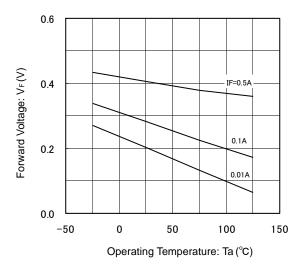
^{*} The device orientation is fixed in its embossed tape pocket.

■TYPICAL PERFORMANCE CHARACTERISTICS

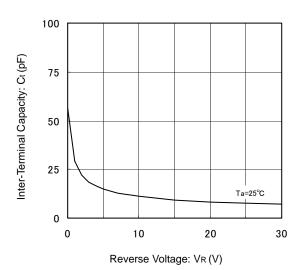
(1) Forward Current vs. Forward Voltage



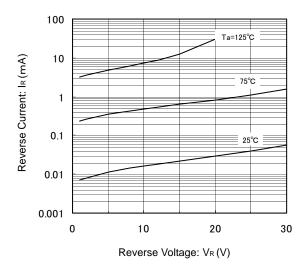
(3) Forward Voltage vs. Operating Temperature



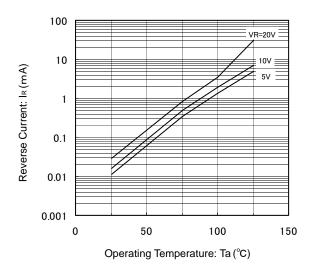
(5) Inter-Terminal Capacity vs. Reverse Voltage



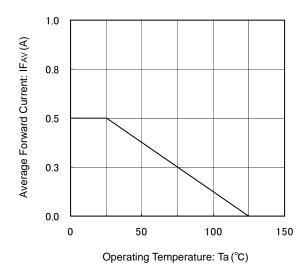
(2) Reverse Current vs. Reverse Voltage



(4) Reverse Current vs. Operating Temperature



(6) Average Forward Current vs. Operating Temperature



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